



STP9NK80Z STF9NK80Z

N-CHANNEL 800V -0.9Ω - 7.5A TO-220/TO-220FP Zener-Protected SuperMESH™ MOSFET

Table 1: General Features

| TYPE | V _{DSS} | R _{DS(on)} | I _D | P _w |
|-----------|------------------|---------------------|----------------|----------------|
| STP9NK80Z | 800 V | <1.2 Ω | 7.5 A | 150 W |
| STF9NK80Z | 800 V | <1.2 Ω | 7.5 A | 35 W |

- TYPICAL R_{DS(on)} = 0.9Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- IMPROVED ESD CAPABILITY
- 100% AVALANCHE RATED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATIBILITY

DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES
- SMPS

Figure 1: Package

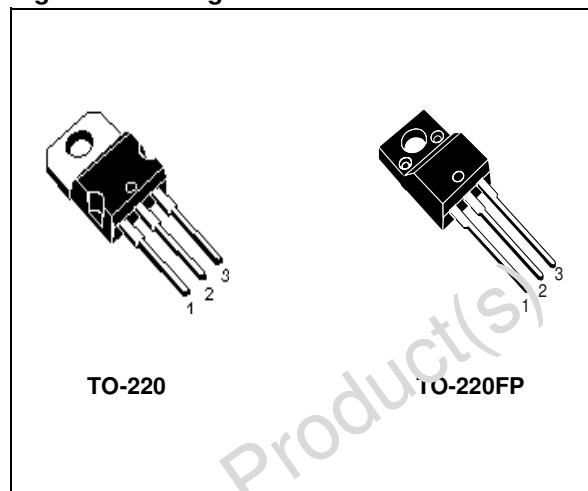


Figure 2: Internal Schematic Diagram

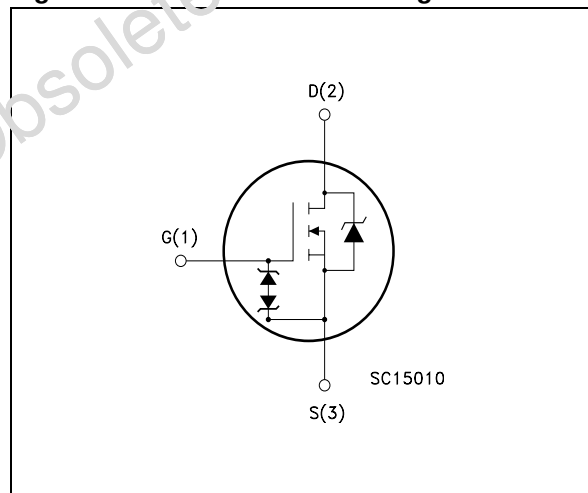


Table 2: Order Codes

| SALES TYPE | MARKING | PACKAGE | PACKAGING |
|------------|---------|----------|-----------|
| STP9NK80Z | P9NK80Z | TO-220 | TUBE |
| STF9NK80Z | F9NK80Z | TO-220FP | TUBE |

Table 3: Absolute Maximum ratings

| Symbol | Parameter | Value | | Unit |
|--------------------|---|--------------------------|----------|--------------------------------------|
| | | TO-220 | TO-220FP | |
| V_{DS} | Drain-source Voltage ($V_{GS} = 0$) | 800 | | V |
| V_{DGR} | Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$) | 800 | | V |
| V_{GS} | Gate- source Voltage | ± 30 | | V |
| I_D | Drain Current (continuous) at $T_C = 25^\circ\text{C}$ | 7.5 | 7.5 (*) | A |
| I_D | Drain Current (continuous) at $T_C = 100^\circ\text{C}$ | 4.7 | 4.7 (*) | A |
| $I_{DM}(\bullet)$ | Drain Current (pulsed) | 30 | 30 (*) | A |
| P_{TOT} | Total Dissipation at $T_C = 25^\circ\text{C}$ | 150 | 35 | W |
| | Derating Factor | 1.20 | 0.28 | W/ $^\circ\text{C}$ |
| $V_{ESD(G-S)}$ | Gate source ESD(HBM-C=100pF, R=1.5K Ω) | 4000 | | V |
| dv/dt (1) | Peak Diode Recovery voltage slope | 4.5 | | V/ns |
| V_{ISO} | Insulation Withstand Voltage (DC) | - | 2500 | V |
| T_j T_{stg} | Operating Junction Temperature Storage Temperature | -55 to 150 -55 to 150 | | $^\circ\text{C}$ $^\circ\text{C}$ |

(●) Pulse width limited by safe operating area

(1) $I_{SD} \leq 7.5\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$

(*) Limited only by maximum temperature allowed

Table 4: Thermal Data

| | | TO-220 | TO-220FP | |
|-----------|--|--------|----------|---------------------------|
| Rthj-case | Thermal Resistance Junction-case Max | 0.83 | 3.6 | $^\circ\text{C}/\text{W}$ |
| Rthj-amb | Thermal Resistance Junction-ambient Max | 62.5 | | $^\circ\text{C}/\text{W}$ |
| T_l | Maximum Lead Temperature For Soldering Purpose | 350 | | $^\circ\text{C}$ |

Table 5: Avalanche Characteristics

| Symbol | Parameter | Max Value | Unit |
|----------|--|-----------|------|
| I_{AR} | Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max) | 7.5 | A |
| E_{AS} | Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$) | 350 | mJ |

Table 6: Gate-Source Zener Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|------------|-------------------------------|--|------|------|------|------|
| BV_{GSO} | Gate-Source Breakdown Voltage | $I_{gs} = \pm 1\text{mA}$ (Open Drain) | 30 | | | V |

PROTECTION FEATURES OF GATE-TO-SOURCE ZENER DIODES

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^{\circ}C$ UNLESS OTHERWISE SPECIFIED)**Table 7: On/Off**

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|----------|--------------------|
| $V_{(BR)DSS}$ | Drain-source Breakdown Voltage | $I_D = 1 \text{ mA}, V_{GS} = 0$ | 800 | | | V |
| I_{DSS} | Zero Gate Voltage Drain Current ($V_{GS} = 0$) | $V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}, T_C = 125^{\circ}C$ | | | 1 50 | μA μA |
| I_{GSS} | Gate-body Leakage Current ($V_{DS} = 0$) | $V_{GS} = \pm 20V$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 100\mu A$ | 3 | 3.75 | 4.5 | V |
| $R_{DS(on)}$ | Static Drain-source On Resistance | $V_{GS} = 10V, I_D = 3.75 \text{ A}$ | | 0.9 | 1.2 | Ω |

Table 8: DYNAMIC

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|---|---|---|------|----------------------|------|----------------------|
| g_{fs} (1) | Forward Transconductance | $V_{DS} = 15 \text{ V}, I_D = 3.75 \text{ A}$ | | 7.5 | | S |
| C_{iss} C_{oss} C_{rss} | Input Capacitance Output Capacitance Reverse Transfer Capacitance | $V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$ | | 1900 180 38 | | pF pF pF |
| $C_{oss \text{ eq.}}$ (3) | Equivalent Output Capacitance | $V_{GS} = 0V, V_{DS} = 0V \text{ to } 640V$ | | 75 | | pF |
| $t_{d(on)}$ t_r $t_{d(off)}$ t_f | Turn-on Delay Time Rise Time Turn-off Delay Time Fall Time | $V_{DD} = 400 \text{ V}, I_D = 3.75 \text{ A}$ $R_G = 4.7\Omega, V_{GS} = 10 \text{ V}$ (see Figure 19) | | 26 19 58 18 | | ns ns ns ns |
| $t_r(V_{off})$ t_f t_c | Off-voltage Rise Time Fall Time Cross-over Time | $V_{DD} = 640 \text{ V}, I_D = 7.5A,$ $R_G = 4.7\Omega, V_{GS} = 10V$ (see Figure 20) | | 12 10 24 | | ns ns ns |
| Q_g Q_{gs} Q_{gd} | Total Gate Charge Gate-Source Charge Gate-Drain Charge | $V_{DD} = 640V, I_D = 7.5 \text{ A},$ $V_{GS} = 10V$ (see Figure 22) | | 60 12 35 | 84 | nC nC nC |

Table 9: Source Drain Diode

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------------------------------|--|---|------|------------------|-----------|--------------------|
| I_{SD} I_{SDM} (2) | Source-drain Current Source-drain Current (pulsed) | | | | 7.5 30 | A A |
| V_{SD} (1) | Forward On Voltage | $I_{SD} = 7.5 \text{ A}, V_{GS} = 0$ | | | 1.6 | V |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 7.5 \text{ A}, di/dt = 100A/\mu s$ $V_{DD} = 35V, T_j = 25^{\circ}C$ (see Figure 20) | | 530 4.5 17 | | ns μC A |
| t_{rr} Q_{rr} I_{RRM} | Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current | $I_{SD} = 7.5 \text{ A}, di/dt = 100A/\mu s$ $V_{DD} = 35V, T_j = 150^{\circ}C$ (see Figure 20) | | 690 6.4 17 | | ns μC A |

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

2. Pulse width limited by safe operating area.

3. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Figure 3: Safe Operating Area for TO-220

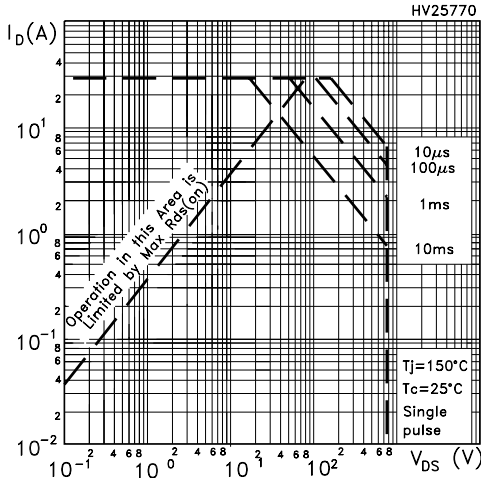


Figure 4: Safe Operating Area for TO-220FP

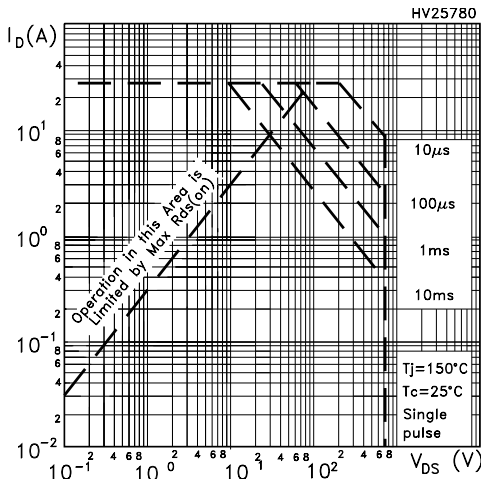


Figure 5: Output Characteristics

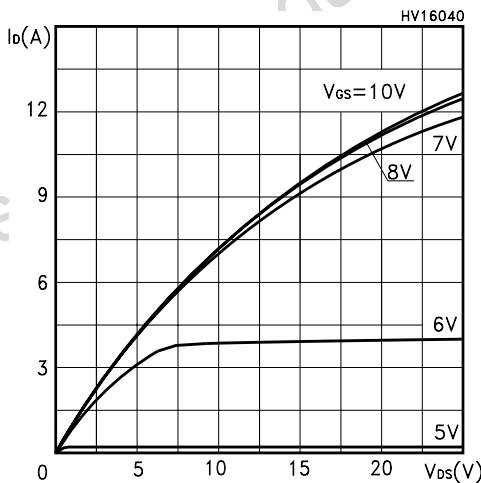


Figure 6: Thermal Impedance for TO-220

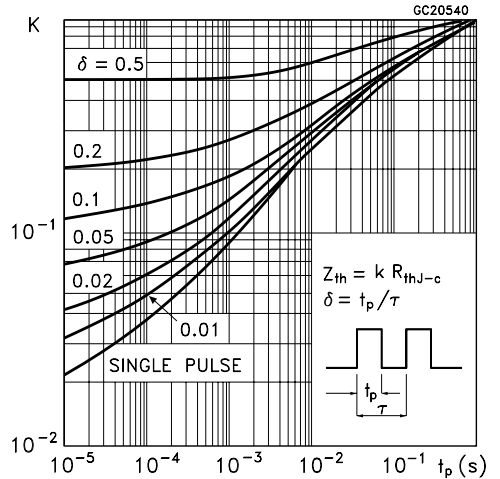


Figure 7: Thermal Impedance for TO-220FP

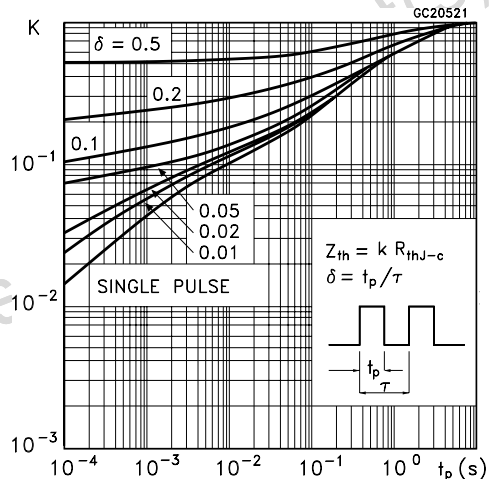


Figure 8: Transfer Characteristics

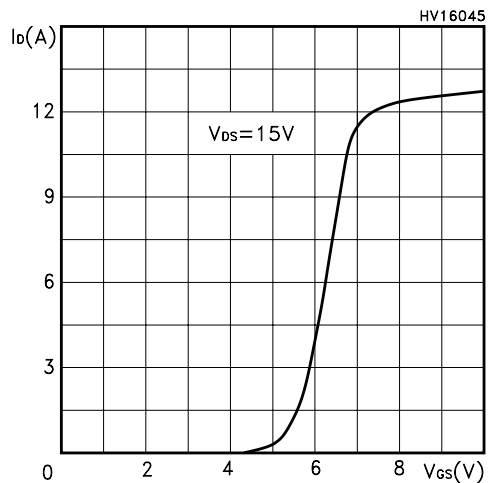


Figure 9: Transconductance

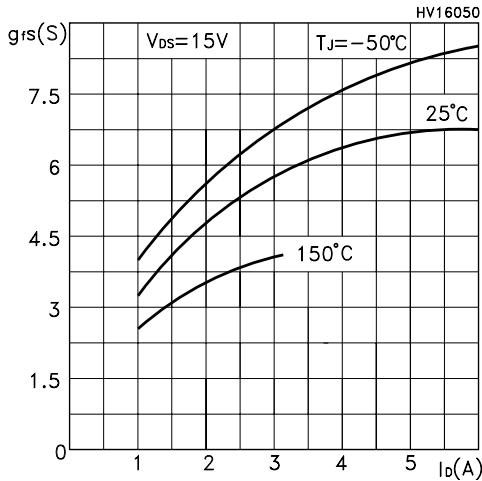


Figure 10: Gate Charge vs Gate-source Voltage

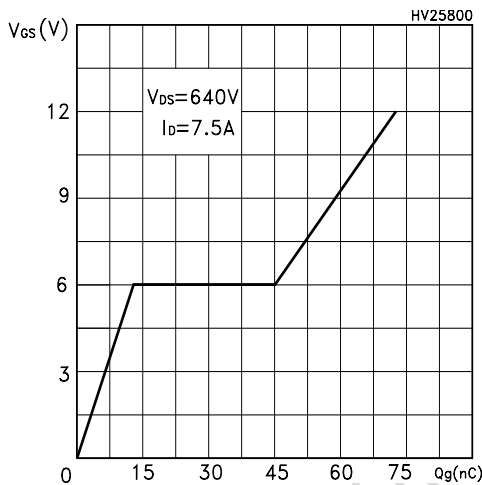


Figure 11: Normalized Gate Threshold Voltage vs Temperature

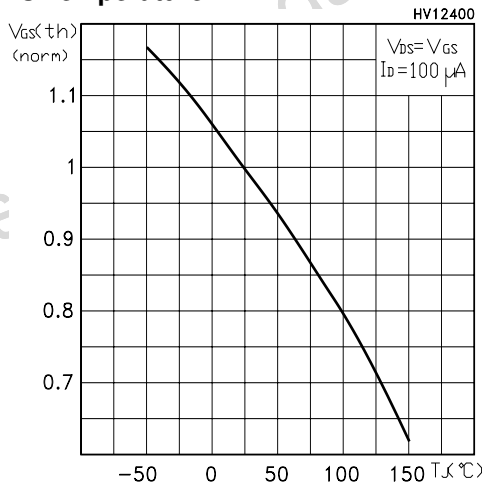


Figure 12: Static Drain-source On Resistance

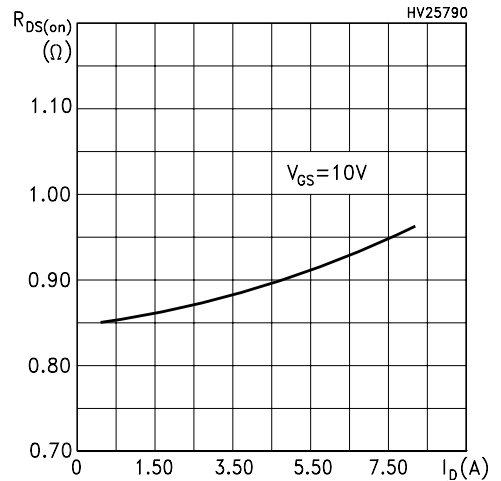


Figure 13: Capacitance Variations

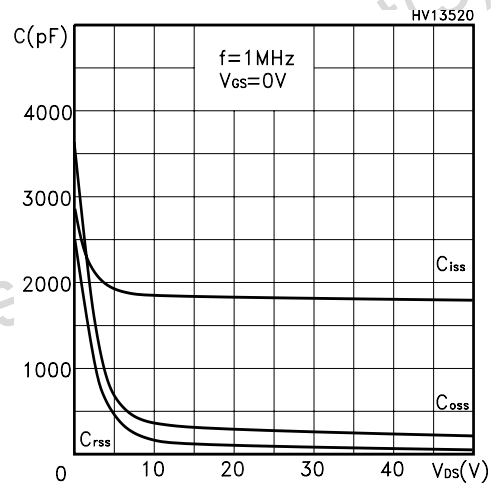


Figure 14: Normalized BVDSS vs Temperature

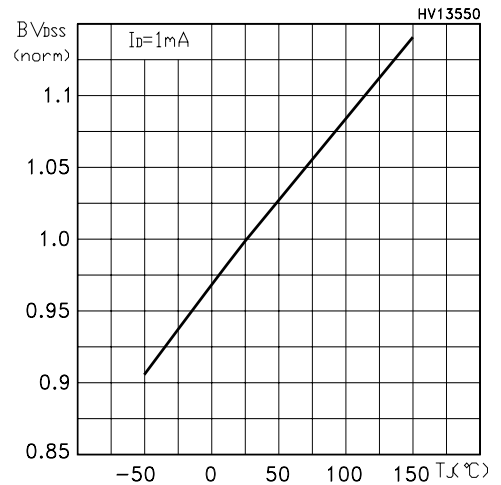


Figure 15: Normalized On Resistance vs TemperatureS

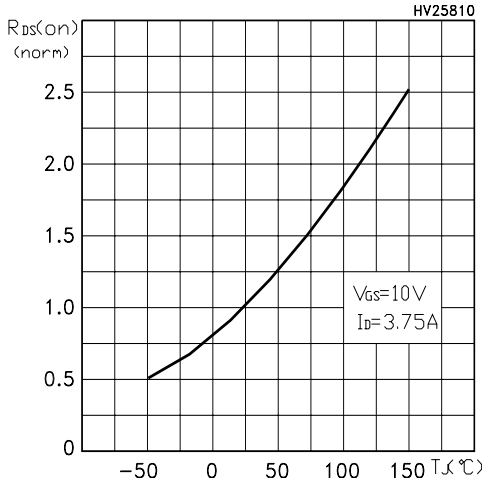


Figure 16: Avalanche Energy vs Temperature

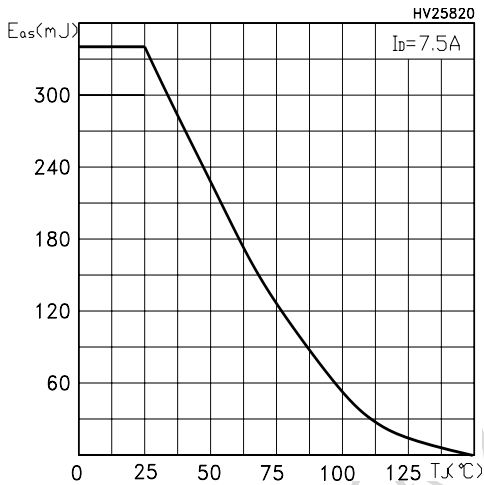


Figure 17: Source-Drain Diode Forward Characteristics

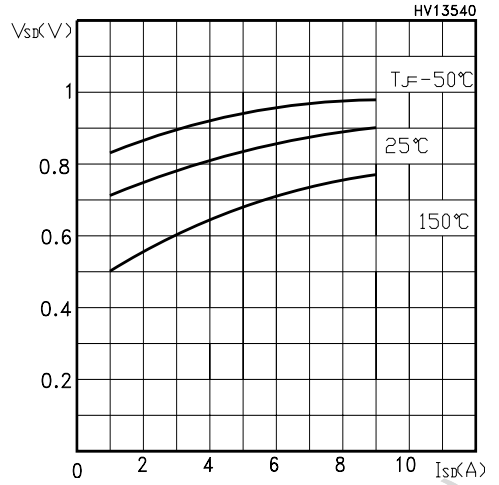


Figure 18: Unclamped Inductive Load Test Circuit

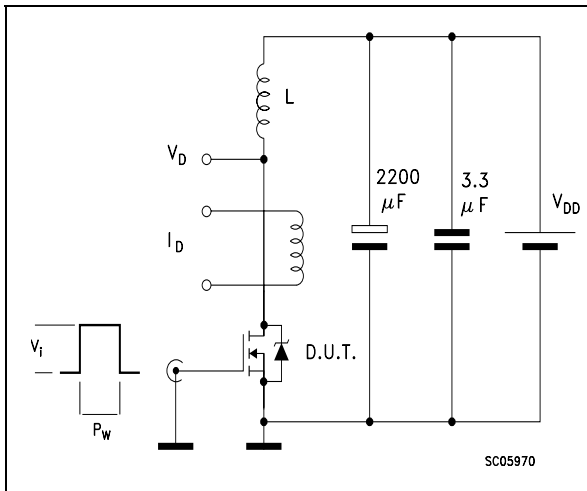


Figure 19: Switching Times Test Circuit For Resistive Load

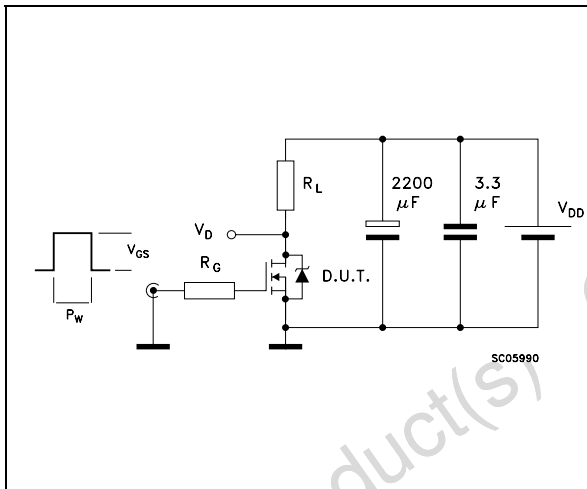


Figure 20: Test Circuit For Inductive Load Switching and Diode Recovery Times

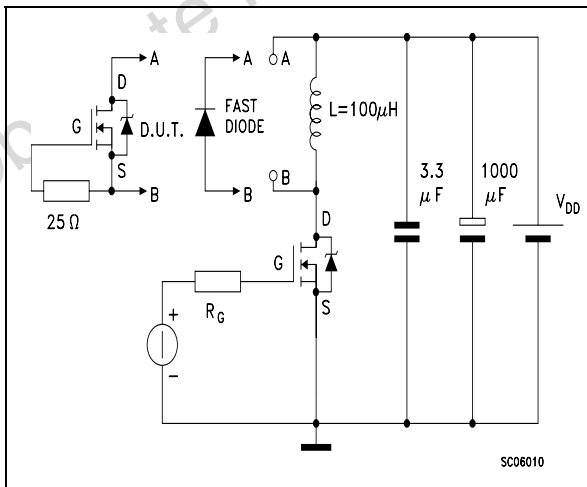


Figure 21: Unclamped Inductive Waferform

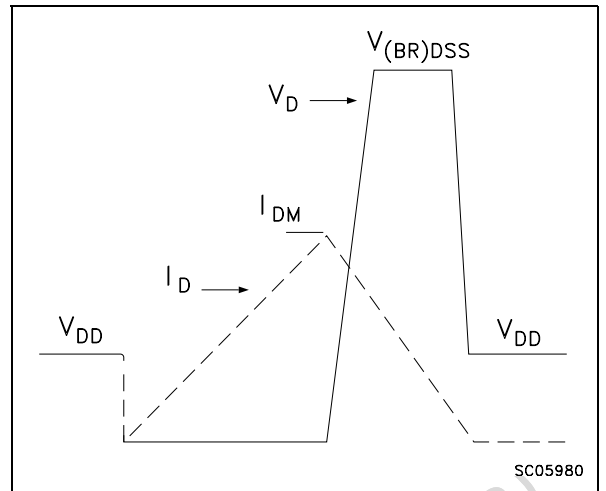
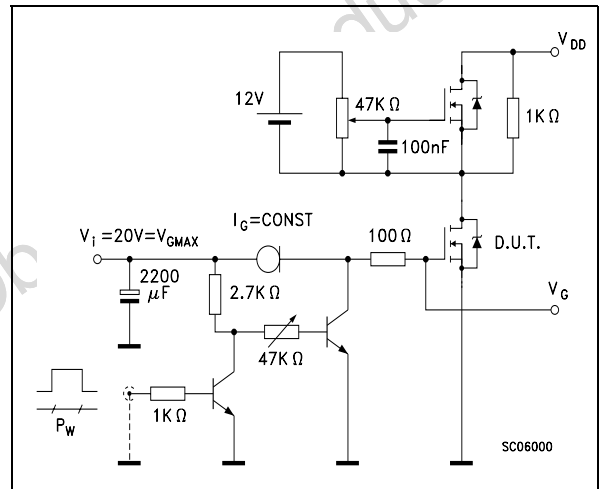
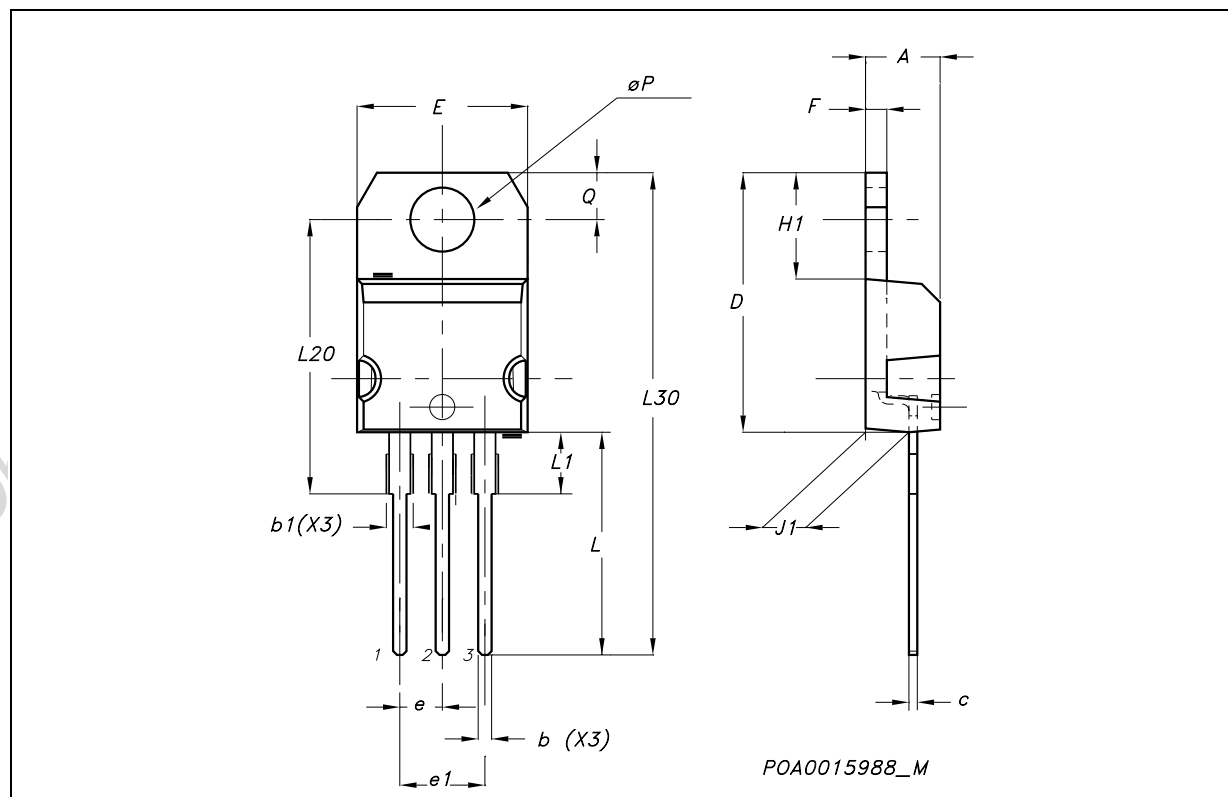


Figure 22: Gate Charge Test Circuit



TO-220 MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|-------|-------|-------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.40 | | 4.60 | 0.173 | | 0.181 |
| b | 0.61 | | 0.88 | 0.024 | | 0.034 |
| b1 | 1.15 | | 1.70 | 0.045 | | 0.066 |
| c | 0.49 | | 0.70 | 0.019 | | 0.027 |
| D | 15.25 | | 15.75 | 0.60 | | 0.620 |
| E | 10 | | 10.40 | 0.393 | | 0.409 |
| e | 2.40 | | 2.70 | 0.094 | | 0.106 |
| e1 | 4.95 | | 5.15 | 0.194 | | 0.202 |
| F | 1.23 | | 1.32 | 0.048 | | 0.052 |
| H1 | 6.20 | | 6.60 | 0.244 | | 0.256 |
| J1 | 2.40 | | 2.72 | 0.094 | | 0.107 |
| L | 13 | | 14 | 0.511 | | 0.551 |
| L1 | 3.50 | | 3.93 | 0.137 | | 0.154 |
| L20 | | 16.40 | | | 0.645 | |
| L30 | | 28.90 | | | 1.137 | |
| øP | 3.75 | | 3.85 | 0.147 | | 0.151 |
| Q | 2.65 | | 2.95 | 0.104 | | 0.116 |



TO-220FP MECHANICAL DATA

| DIM. | mm. | | | inch | | |
|------|------|------|------|-------|-------|-------|
| | MIN. | TYP. | MAX. | MIN. | TYP. | MAX. |
| A | 4.4 | | 4.6 | 0.173 | | 0.181 |
| B | 2.5 | | 2.7 | 0.098 | | 0.106 |
| D | 2.5 | | 2.75 | 0.098 | | 0.108 |
| E | 0.45 | | 0.7 | 0.017 | | 0.027 |
| F | 0.75 | | 1 | 0.030 | | 0.039 |
| F1 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| F2 | 1.15 | | 1.7 | 0.045 | | 0.067 |
| G | 4.95 | | 5.2 | 0.195 | | 0.204 |
| G1 | 2.4 | | 2.7 | 0.094 | | 0.106 |
| H | 10 | | 10.4 | 0.393 | | 0.409 |
| L2 | | 16 | | | 0.630 | |
| L3 | 28.6 | | 30.6 | 1.126 | | 1.204 |
| L4 | 9.8 | | 10.6 | .0385 | | 0.417 |
| L5 | 2.9 | | 3.6 | 0.114 | | 0.141 |
| L6 | 15.9 | | 16.4 | 0.626 | | 0.645 |
| L7 | 9 | | 9.3 | 0.354 | | 0.366 |
| Ø | 3 | | 3.2 | 0.118 | | 0.126 |

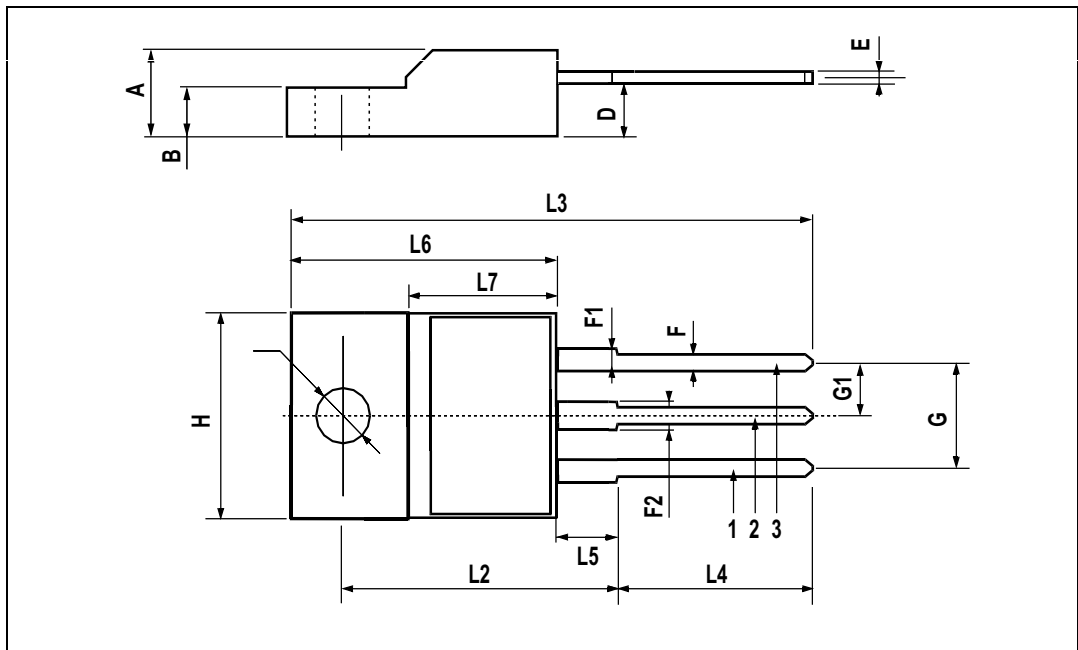


Table 10: Revision History

| Date | Revision | Description of Changes |
|-------------|----------|------------------------|
| 18-May-2005 | 1 | First Release. |

Obsolete Product(s) - Obsolete Product(s)

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